

# TRSF3221E 3V to 5.5V Single-Channel RS-232 1Mbit Line Driver and Receiver With ±15kV IEC ESD Protection in Small Package

#### 1 Features

- ESD protection for RS-232 pins
  - ±15kV Human-body model (HBM)
  - ±8kV IEC 61000-4-2 Contact discharge
  - ±15kV IEC 61000-4-2 Air-gap discharge
- Operates with 3V to 5.5V V<sub>CC</sub> supply
- Operates up to 1Mbit/s
  - Low-speed pin-compatible device (250kbit/s) TRS3221E
- Available in near chip-scale package, 16-pin VQFN (RGT, 82% smaller than TSSOP package)
- Low standby current: 1µA typical
- External capacitors: 4 × 0.1µF
- Accepts 5V logic input with 3.3V supply
- Auto-powerdown feature automatically disables drivers for power savings

## 2 Applications

- Industrial PCs
- Wired networking
- Data center and enterprise computing
- Battery-powered systems
- **PDAs**
- **Notebooks**
- Laptops
- Palmtop PCs
- Hand-held equipment

## 3 Description

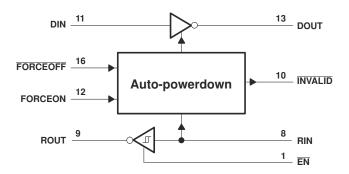
The TRSF3221E consists of one line driver, one line receiver, and a dual charge-pump circuit with ±15kV IEC ESD protection pin to pin (serial-port connection pins, including GND). The TRSF3221E provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3V to 5.5V supply. The TRSF3221E operates at data signaling rates up to 1Mbit/s and a driver output slew rate of 24V/µs to 150V/µs.

Flexible control options for power management are available when the serial port is inactive. The autopowerdown feature functions when FORCEON is low and FORCEOFF is high. During this mode of operation, if the TRSF3221E does not sense a valid RS-232 signal on the receiver input, the driver output is disabled. If FORCEOFF is set low and the enable (EN) input is high, both the driver and receiver are shut off, and the supply current is reduced to 1µA. Disconnecting the serial port or turning off the peripheral drivers causes the auto-powerdown condition to occur. Auto-powerdown can be disabled when FORCEON and FORCEOFF are high. With auto-powerdown enabled, the device is activated automatically when a valid signal is applied to the receiver input. The INVALID output notifies the user if an RS-232 signal is present at the receiver input. INVALID is high (valid data) if the receiver input voltage is greater than 2.7V or less than -2.7V, or has been between -0.3V and 0.3V for less than 30µs. INVALID is low (invalid data) if the receiver input voltage is between -0.3V and 0.3V for more than 30µs. See Figure 6-5 for receiver input levels.

#### **Package Information**

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE(2)
	DB (SSOP)	6.2mm x 5.3mm
TRSF3221F	PW (TSSOP)	5mm x 4.4mm
TROI 3221L	RGT (VQFN)	3mm x 3mm
	SOT-23-THN (DYY, 16)	4.2mm × 2mm

- For more information, see Section 11. (1)
- The package size (length × width) is a nominal value and includes pins, where applicable.



Logic Diagram (Positive Logic)



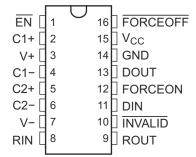
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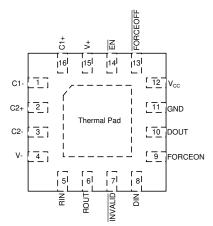
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# **4 Pin Configuration and Functions**



DB or PW Package. 16 Pins (Top View)



**RGT, VSON Package, 16 Pins (Top View)** 

**Table 4-1. Pin Functions** 

	PIN			PIN			DESCRIPTION
NAME	DB or PW	RGT	ITPE	DESCRIPTION POLIT			
EN	1	14		Low input enables receiver ROUT output. High input sets ROUT to high impedance.			
C1+	2	16	-	Positive lead of C1 capacitor			
V+	3	15	0	Positive charge pump output for storage capacitor only			
C1-	4	1	-	Negative lead of C1 capacitor			
C2+	5	2	-	Positive lead of C2 capacitor			
C2-	6	3	-	Negative lead of C2 capacitor			
V-	7	4	0	Negative charge pump output for storage capacitor only			
RIN	8	5	1	RS232 line data input (from remote RS232 system)			
ROUT	9	6	0	Logic data output (to UART)			
INVALID	10	7		Invalid output pin. Output low when RIN input is unpowered.			
DIN	11	8	1	Logic data input (from UART)			
FORCEON	12	9		Automatic power-down control input			
DOUT	13	10	0	RS232 line data output (to remote RS232 system)			
GRD	14	11	-	Ground			
V <sub>CC</sub>	15	12	-	Supply Voltage, Connect to external 3V to 5.5V power supply			
FORCEOFF	16	13		Automatic power-down control input			
Thermal Pad	-	Yes	-	Exposed thermal pad. Can be connected to GND or left floating.			

<sup>(1)</sup> Signal Types: I = Input, O = Output, I/O = Input or Output.



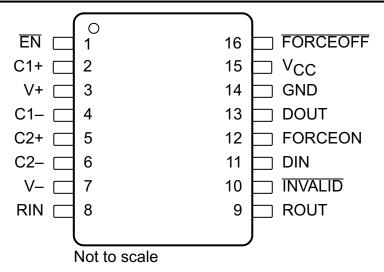


Figure 4-1. DYY Package 16-Pin SOT-23-THN (Top View)

**Table 4-2. Pin Functions** 

PIN		TVDE	DECORIDATION		
NAME	NO.	TYPE	DESCRIPTION		
EN	1	I	Low input enables receiver ROUT output. High input sets ROUT to high impedance.		
C1+	2	_	Positive terminals of the voltage-doubler charge pump capacitors		
V+	3	0	5.5V supply generated by the charge pump		
C1–	4	_	Negative terminals of the voltage-doubler charge pump capacitors		
C2+	5		Positive terminals of the voltage-doubler charge pump capacitors		
C2-	6		Negative terminals of the voltage-doubler charge pump capacitors		
V-	7	0	-5.5V supply generated by the charge pump		
RIN	8	I	RS-232 receiver input		
ROUT	9	0	Receiver output		
INVALID	10	0	Invalid output pin. Output low when RIN input is unpowered.		
DIN	11	I	Driver input		
FORCEON	12	I	Automatic power-down control input		
DOUT	13	0	RS-232 driver output		
GND	14	_	Ground		
V <sub>CC</sub>	15	_	3V to 5.5V supply voltage		
FORCEOFF	16	1	Automatic power-down control input		

## 5 Specifications

## 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)See (1)

	3 1 3 (	·	MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range <sup>(2)</sup>		-0.3	6	V
V+	Positive output supply voltage range <sup>(2)</sup>		-0.3	7	V
V-	Negative output supply voltage range <sup>(2)</sup>			-7	V
V+ – V–	Supply voltage difference <sup>(2)</sup>			13	V
V	Input voltage range	Driver ( FORCEOFF, FORCEON, EN)		6	V
V <sub>I</sub>	Input voltage range	Receiver	-25	25	v
V	Output valtage range	Driver		13.2	V
Vo	Output voltage range  Receiver ( INVALID)		-0.3	V <sub>CC</sub> + 0.3	V
TJ	Operating virtual junction temperature			150	°C
T <sub>stg</sub>	Storage temperature range		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 5.2 ESD Ratings

			VALUE	UNIT
V <sub>(ESD)</sub> Electrostatic discha	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±3000	V
	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1500	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

## 5.3 ESD Ratings, IEC Specifications

PIN NAME	TEST CONDITIONS	VALUE	UNIT
	НВМ	±15,000	
RIN, DOUT <sup>(2)</sup>	IEC 61000-4-2 Contact Discharge <sup>(1) (2)</sup>	±8,000	V
	IEC 61000-4-2 Air-Gap Discharge <sup>(1)</sup> (2)	±15,000	

<sup>(1)</sup> For the RGT and PW package only, a minimum of 1µF capacitor is required between VCC and GND to meet the specified IEC-ESD level

<sup>(2)</sup> All voltages are with respect to network GND.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

<sup>(2)</sup> For optimized IEC ESD performance for DYY package, the recommendation is to have series resistor (≥ 50Ω), on all logic inputs directly connected to power or ground, to minimize the transient currents going into or out of the logic pins.



## 5.4 Recommended Operating Conditions

See Figure 8-1 and (1)

				MIN	NOM	MAX	UNIT
	Supply voltage		V <sub>CC</sub> = 3.3 V	3	3.3	3.6	V
	Supply Vollage			4.5	5	5.5	V
V	Driver and control	er and control DIN, FORCEOFF, FORCEON, EN		2			V
V <sub>IH</sub>	high-level input voltage	evel input voltage	V <sub>CC</sub> = 5 V	2.4			V
V <sub>IL</sub>	Driver and control low-level input voltage	DIN, FORCEOFF, FORCEON, EN				0.8	V
VI	Driver and control input voltage	DIN, FORCEOFF, FORCEON		0		5.5	V
VI	Receiver input voltage			-25		25	V
T <sub>A</sub>	On another from a six to see a section		TRSF3221EI	-40		85	°C
	Operating free-air temperature	TRSF3221EC	0		70	C	

<sup>(1)</sup> Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5 V  $\pm$  0.5 V.

#### 5.5 Thermal Resistance Characteristics

		TRSF3221E					
THERMAL METRIC <sup>(1)</sup>		DB (SSOP)	PW (TSSOP)	RGT (VQFN)	DYY (SOT-23-THN)	UNIT	
		16 Pins	16 Pins	16 Pins	16 Pins	1	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	82	110.9	58.8	119.8	°C/W	
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	45.7	41.7	55.8	56.5	°C/W	
R <sub>θJB</sub>	Junction-to-board thermal resistance	44.4	57.2	23.8	51.5	°C/W	
Ψ ЈТ	Junction-to-top characterization parameter	11.0	4.2	1.7	2.6	°C/W	
Ψ <sub>ЈВ</sub>	Junction-to-board characterization parameter	43.8	56.6	23.7	51.1	°C/W	
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	9	N/A	°C/W	

For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report.

## 5.6 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 8-1)

	PARA	METER	TEST CONDITIONS <sup>(1)</sup>	MIN	TYP <sup>(2)</sup>	MAX	UNIT
II	Input leakage current	FORCEOFF, FORCEON, EN			±0.01	±1	μA
		Auto-powerdown disabled	No load, FORCEOFF and FORCEON at V <sub>CC</sub>		0.3	1	mA
lcc	Supply current	Powered off	No load, FORCEOFF at GND		1	10	
I <sub>CC</sub>	$(T_A = 25^{\circ}C)$	Auto-powerdown enabled	No load, FORCEOFF at V <sub>CC</sub> , FORCEON at GND, All RIN are open or grounded		1	10	μA

Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V. All typical values are at V<sub>CC</sub> = 3.3 V or V<sub>CC</sub> = 5 V, and T<sub>A</sub> = 25°C.

#### 5.7 Electrical Characteristics, Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 8-1)

	PARAMETER	TEST CONDITIONS <sup>(1)</sup>				TYP <sup>(2)</sup>	MAX	UNIT
V <sub>OH</sub>	High-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	DIN = GND		5	5.4		V
V <sub>OL</sub>	Low-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	DIN = V <sub>CC</sub>		-5	-5.4		V
I <sub>IH</sub>	High-level input current	V <sub>I</sub> = V <sub>CC</sub>				±0.01	±1	μA
I <sub>IL</sub>	Low-level input current	V <sub>I</sub> at GND				±0.01	±1	μΑ
	Short-circuit output current <sup>(3)</sup>	V <sub>CC</sub> = 3.6 V,	V <sub>O</sub> = 0 V			±35	±60	mA
los		V <sub>CC</sub> = 5.5 V,	V <sub>O</sub> = 0 V			±35	±90	
ro	Output resistance	V <sub>CC</sub> , V+, and V– = 0 V,	V <sub>O</sub> = ±2 V		300	10M		Ω
	Output leakage current	t leakage current FORCEOFF = GND	V <sub>O</sub> = ±12 V,	$V_{CC}$ = 3 V to 3.6 V			±25	
I <sub>off</sub>			$V_0 = \pm 10 \text{ V},$	V <sub>CC</sub> = 4.5 V to 5.5 V			±25	μA

- (1) Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.
- (2) All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25 ^{\circ}\text{C}$ .
- (3) Short-circuit durations must be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output can be shorted at a time.

## 5.8 Switching Characteristics, Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 8-1)

<u> </u>	iguio o 1)								
ı	PARAMETER		TEST CONDITIONS		MIN	TYP <sup>(2)</sup>	MAX	UNIT	
Maximum data rate (see Figure 6-1)			C <sub>L</sub> = 1000 pF		250				
		$R_L = 3 k\Omega$	C <sub>L</sub> = 250 pF,	V <sub>CC</sub> = 3 V to 4.5 V	1000			kbit/s	
(00011	guio o 1 /		C <sub>L</sub> = 1000 pF,	V <sub>CC</sub> = 4.5 V to 5.5 V	1000				
	Pulse skew <sup>(3)</sup>	C <sub>L</sub> = 250 pF		$R_L$ = 3 kΩFigure 6-2	RGT Package		25		
t <sub>sk(p)</sub>		C <sub>L</sub> = 150 pF to 2500 pF,	$R_L$ = 3 kΩ to 7 kΩ, See Figure 6-2	DB or PW package		100		ns	
SR(tr)	Slew rate, transition region (see Figure 6-1)	V <sub>CC</sub> = 3.3 V,	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$	C <sub>L</sub> = 150 pF to 1000 pF	18		150	V/µs	

- (1) Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5 V  $\pm$  0.5 V.
- (2) All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .
- (3) Pulse skew is defined as |t<sub>PLH</sub> t<sub>PHL</sub>| of each channel of the same device.



## 5.9 Electrical Characteristics, Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 8-1)

	PARAMETER	TEST CONDITIONS(1)	MIN	TYP <sup>(2)</sup>	MAX	UNIT
V <sub>OH</sub>	High-level output voltage	I <sub>OH</sub> = -1 mA	V <sub>CC</sub> – 0.6 V	V <sub>CC</sub> – 0.1 V		V
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 1.6 mA			0.4	V
V <sub>IT+</sub>	Positive-going input threshold voltage	V <sub>CC</sub> = 3.3 V		1.6	2.4	V
V IT+	Positive-going input the short voltage	V <sub>CC</sub> = 5 V		1.9	2.4	V
V	Negative-going input threshold voltage	V <sub>CC</sub> = 3.3 V	0.6	1.1		V
V <sub>IT</sub>	Negative-going input tilleshold voltage	V <sub>CC</sub> = 5 V	0.8	1.4		V
V <sub>hys</sub>	Input hysteresis (V <sub>IT+</sub> – V <sub>IT-</sub> )			0.5		V
I <sub>off</sub>	Output leakage current	FORCEOFF = 0 V		±0.05	±10	μΑ
r <sub>i</sub>	Input resistance	V <sub>I</sub> = ±3 V to ±25 V	3	5	7	kΩ

- Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5 V ± 0.5 V.
- All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25 ^{\circ}\text{C}$ .

#### 5.10 Switching Characteristics, Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 8-1)

	PARAMETER	TEST CO	TEST CONDITIONS(1)			
	Dropogation delay time law to high layer output	C <sub>L</sub> = 150 pF, See	RGT package	100		
t <sub>PLH</sub>	Propagation delay time, low- to high-level output	Figure 6-3	DB or PW package	150	ns	
	Dropogation delay time high to law lovel output	C <sub>L</sub> = 150 pF, See	RGT package	125	200	
t <sub>PHL</sub>	Propagation delay time, high- to low-level output	Figure 6-3	DB or PW package	150	ns	
t <sub>en</sub>	Output enable time	C <sub>L</sub> = 150 pF, R <sub>L</sub> = 3	$C_L$ = 150 pF, $R_L$ = 3 k $\Omega$ , See Figure 6-4		ns	
t <sub>dis</sub>	Output disable time	C <sub>L</sub> = 150 pF, R <sub>L</sub> = 3	kΩ, See Figure 6-4	200	ns	
4	Pulse skew <sup>(3)</sup>	See Figure 6-3	RGT package	25	200	
t <sub>sk(p)</sub>	Fuise Skew	See Figure 6-3	DB or PW package	50	ns	

- Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V. All typical values are at V<sub>CC</sub> = 3.3 V or V<sub>CC</sub> = 5 V, and T<sub>A</sub> = 25°C. Pulse skew is defined as  $|t_{PLH} t_{PHL}|$  of each channel of the same device. (1)

#### 5.11 Electrical Characteristics, Auto-Powerdown

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 6-5)

(1000 · 1.94.10 0 0)										
	PARAMETER	TEST CON	MIN	MAX	UNIT					
V <sub>T+(valid)</sub>	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND,	FORCEOFF = V <sub>CC</sub>		2.7	V				
V <sub>T-(valid)</sub>	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND,	FORCEOFF = V <sub>CC</sub>	-2.7		V				
V <sub>T(invalid)</sub>	Receiver input threshold for INVALID low-level output voltage	FORCEON = GND,	FORCEOFF = V <sub>CC</sub>	-0.3	0.3	V				
V <sub>OH</sub>	INVALID high-level output voltage	I <sub>OH</sub> = -1 mA, FORCEON FORCEOFF = V <sub>CC</sub>	V <sub>CC</sub> - 0.6		V					
V <sub>OL</sub>	INVALID low-level output voltage	I <sub>OL</sub> = 1.6 mA, FORCEON FORCEOFF = V <sub>CC</sub>	N = GND,		0.4	V				

## 5.12 Switching Characteristics, Auto-Powerdown

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 6-5)

	PARAMETER	TYP <sup>(1)</sup>	UNIT
t <sub>valid</sub>	Propagation delay time, low- to high-level output	1	μs
t <sub>invalid</sub>	Propagation delay time, high- to low-level output	30	μs
t <sub>en</sub>	Supply enable time	100	μs

(1) All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C.

## 5.13 Typical Characteristics

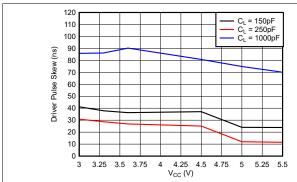


Figure 5-1. Driver Pulse Skew vs Load Capacitance and Supply Voltage at  $T_A$  = 25°C (RGT Package)

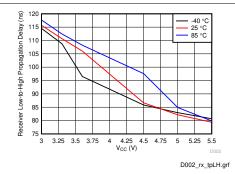


Figure 5-2. Receiver Path Low-to-High Propagation Delay vs T<sub>A</sub> and Supply Voltage (RGT Package)

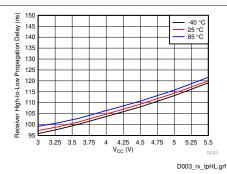


Figure 5-3. . Receiver Path High-to-Low Propagation Delay vs TA and Supply Voltage (RGT Package)

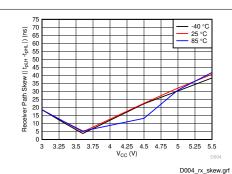
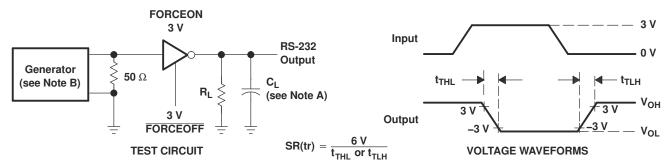


Figure 5-4. Receiver Pulse Skew (|t<sub>pLH</sub> - t<sub>pHL</sub>|) vs T<sub>A</sub> and Supply Voltage (RGT Package)



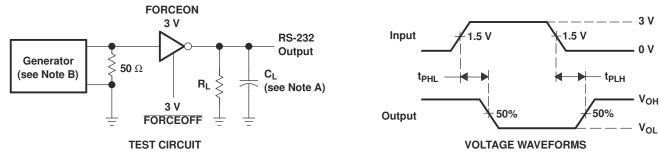
## **6 Parameter Measurement Information**



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_O = 50 \Omega$ , 50% duty cycle,  $t_r \le 10$  ns.  $t_f \le 10$  ns.

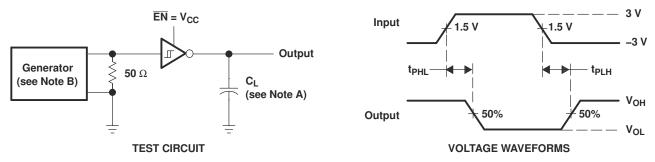
Figure 6-1. Driver Slew Rate



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_O = 50 \Omega$ , 50% duty cycle,  $t_r \le 10$  ns.  $t_f \le 10$  ns.

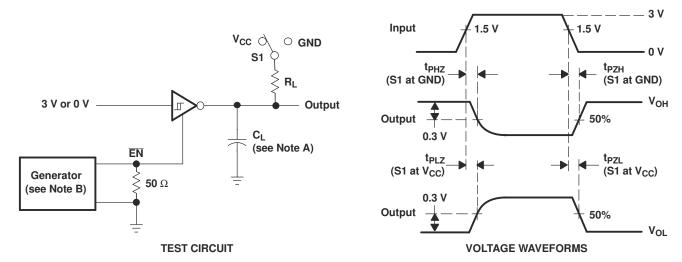
Figure 6-2. Driver Pulse Skew



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics:  $Z_O = 50 \Omega$ , 50% duty cycle,  $t_r \le 10$  ns.  $t_f \le 10$  ns.

Figure 6-3. Receiver Propagation Delay Times



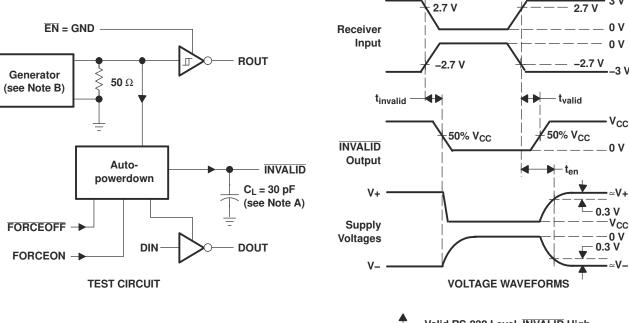
NOTES: A.  $C_L$  includes probe and jig capacitance.

- B. The pulse generator has the following characteristics:  $Z_O = 50~\Omega$ , 50% duty cycle,  $t_r \le 10~ns$ ,  $t_f \le 10~ns$ .
- C.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
- D.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .

Figure 6-4. Receiver Enable and Disable Times



- 3 V



Valid RS-232 Level, INVALID High 2.7 V Indeterminate 0.3 V If Signal Remains Within This Region For More Than 30  $\mu$ s,  $\overline{\text{INVALID}}$  Is Low<sup>†</sup> -0.3 V Indeterminate -2.7 V Valid RS-232 Level, INVALID High

NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 5 kbit/s,  $Z_O = 50 \ \Omega$ , 50% duty cycle,  $t_r \le 10$  ns.  $t_f \le 10$  ns.

Figure 6-5. INVALID Propagation Delay Times and Driver Enabling Time

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<sup>†</sup> Auto-powerdown disables drivers and reduces supply current to 1  $\mu$ A.

## 7 Detailed Description

#### 7.1 Overview

The TRSF3221E consists of one line driver, one line receiver, and a dual charge-pump circuit with ±15kV IEC ESD protection pin to pin (serial-port connection pins, including GND). The TRSF3221E provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3V to 5.5V supply. The TRSF3221E operates at data signaling rates up to 1Mbit/s and a driver output slew rate of 24V/µs to 150V/µs.

Flexible control options for power management are available when the serial port is inactive. The autopowerdown feature functions when FORCEON is low and  $\overline{FORCEOFF}$  is high. During this mode of operation, if the TRSF3221E does not sense a valid RS-232 signal on the receiver input, the driver output is disabled. If  $\overline{FORCEOFF}$  is set low and the enable ( $\overline{EN}$ ) input is high, both the driver and receiver are shut off, and the supply current is reduced to 1µA. Disconnecting the serial port or turning off the peripheral drivers causes the auto-powerdown condition to occur. Auto-powerdown can be disabled when FORCEON and  $\overline{FORCEOFF}$  are high. With auto-powerdown enabled, the device is activated automatically when a valid signal is applied to the receiver input. The  $\overline{INVALID}$  output notifies the user if an RS-232 signal is present at the receiver input.  $\overline{INVALID}$  is high (valid data) if the receiver input voltage is greater than 2.7V or less than -2.7V, or has been between -0.3V and 0.3V for less than 30µs.  $\overline{INVALID}$  is low (invalid data) if the receiver input voltage is between -0.3V and 0.3V for more than 30µs. Outputs are protected against shorts to ground.

#### 7.2 Functional Block Diagram

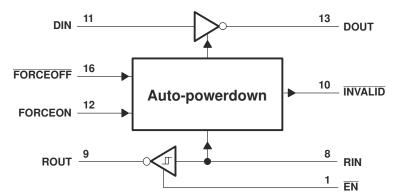


Figure 7-1. Logic Diagram (Positive Logic)

#### 7.3 Feature Description

The power block increases, inverts, and regulates voltage at V+ and V- pins using a charge pump that requires four external capacitors. Auto-power-down feature for driver is controlled by FORCEON and  $\overline{\text{FORCEOFF}}$  inputs. Receiver is controlled by  $\overline{\text{EN}}$  input. When MAX3221E is unpowered, it can be safely connected to an active remote RS-232 device.

The driver interfaces the standard logic level to RS232 voltage levels. The DIN input must be valid high or low.

The receiver interfaces RS-232 levels to standard logic levels. An open input results in a high output on ROUT. RIN input includes an internal standard RS-232 load. A logic high input on the  $\overline{\text{EN}}$  pin shuts down the receiver output.



## 7.4 Device Functional Modes

## **Functional Tables, Each Driver**

	IN	PUTS <sup>(1)</sup>		OUTPUT	
DIN	FORCEON	FORCEOFF	VALID RIN RS-232 LEVEL		DRIVER STATUS
Х	Х	L	Х	Z	Powered off
L	Н	Н	X	Н	Normal operation with
Н	Н	Н	X	L	auto-powerdown disabled
L	L	Н	Yes	Н	Normal operation with
Н	L	Н	Yes	L	auto-powerdown enabled
L	L	Н	No	Z	Powered off by
Н	L	Н	No	Z	auto-powerdown feature

(1) H = high level, L = low level, X = irrelevant, Z = high impedance

## **Each Receiver**

	INPUTS <sup>(1)</sup>									
RIN	ĒN	VALID RIN RS-232 LEVEL	OUTPUT ROUT							
L	L	X	Н							
Н	L	X	L							
Х	Н	X	Z							
Open	L	No	Н							

(1) H = high level, L = low level, X = irrelevant, Z = high impedance (off), Open = disconnected input or connected driver off

Product Folder Links: TRSF3221E

## 8 Application and Implementation

#### Note

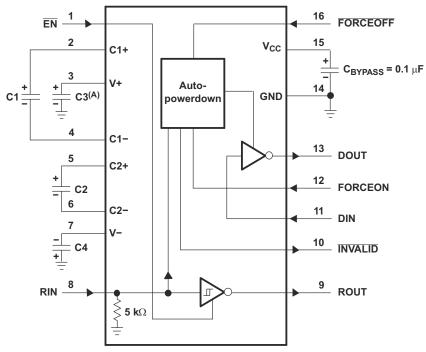
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

## 8.1 Application Information

The TRSF3221E line driver and receiver is a specialized device for 3V to 5.5V RS-232 communication applications. This application is a generic implementation of this device with all required external components. For proper operation, add capacitors as shown in Table 8-1.

## 8.1.1 Typical Application

ROUT and DIN connect to UART or general purpose logic lines. FORCEON and FORCEOFFmay be connected general purpose logic lines or tied to ground or VCC. INVALID may be connected to a general purpose logic line or left unconnected. RIN and DOUT lines connect to a RS-232 connector or cable. DIN, FORCEON, and FORCEOFF inputs must not be left unconnected.



- C3 can be connected to V<sub>CC</sub> or GND.
- Resistor values shown are nominal.
- C. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they must be connected as shown.

Figure 8-1. Typical Operating Circuit and Capacitor Values

Table 8-1. V<sub>CC</sub> vs Capacitor Values

V <sub>CC</sub>	C1	C2, C3, C4
3.3V ± 0.3V	0.1µF	0.1µF
5V ± 0.5V	0.047µF	0.33µF
3V to 5.5V	0.1µF	0.47µF



#### 8.1.1.1 Design Requirements

- Recommended VCC is 3.3V or 5V 3V to 5.5V is also possible
- · Maximum recommended bit rate is 1Mbps
- Use capacitors as shown in Figure 8-1 and Table 8-1

#### 8.1.1.2 Detailed Design Procedure

For proper operation:

- DIN, FORCEOFF and FORCEON inputs must be connected to valid low or high logic levels
- Select capacitor values based on VCC level for best performance

ROUT and DIN connect to UART or general purpose logic lines. FORCEON and FORCEOFF may be connected general purpose logic lines or tied to ground or VCC. INVALID may be connected to a general purpose logic line or left unconnected. RIN and DOUT lines connect to a RS232 connector or cable. DIN, FORCEON, and FORCEOFF inputs must not be left unconnected.

## 8.1.2 Application Performance Plot

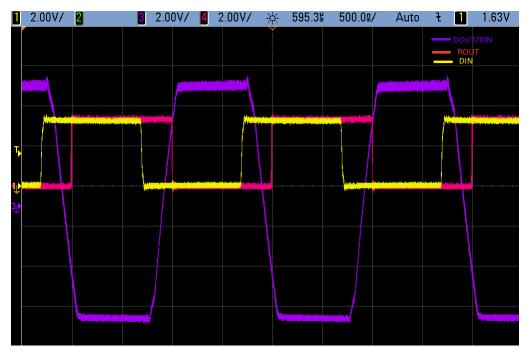


Figure 8-2. 1 Mbps Driver to Receiver Loopback Timing Waveform, V<sub>CC</sub> = 3.3 V

## 8.2 Power Supply Recommendations

V<sub>CC</sub> must be between 3V and 5.5V. Charge pump capacitors must be chosen using V<sub>CC</sub> vs Capacitor Values.

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## 8.3 Layout

## 8.3.1 Layout Guidelines

Keep the external capacitor traces short. This is more important on C1 and C2 nodes, which have the fastest rise and fall times.

#### 8.3.2 Layout Example

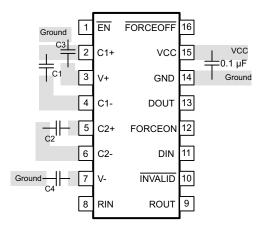


Figure 8-3. Layout Diagram



## 9 Device and Documentation Support

## 9.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

## 9.2 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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#### 9.3 Trademarks

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## 9.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## 9.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

#### 10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (July 2021) to Revision C (December 2024)	Page
Changed the Device Information table to the Package Information table	1
Added the SOT-23-THN (DYY) package to the data sheet	1
Added Note 2 to the ESD Ratings, IEC Specifications	
Changes from Revision A (May 2021) to Revision B (July 2021)	Page
Changed the Applications list	1
Changed the table note for the ESD Ratings, IEC Specifications table to make it also applications.	
PW package	5
Changed the thermal information for PW package	
Changes from Revision * (August 2007) to Revision A (May 2021)	Page
<ul> <li>Added Device Information table, ESD Ratings table, Feature Description section, Device Fur Application and Implementation section, Power Supply Recommendations section, Layout so and Documentation Support section, and Mechanical, Packaging, and Orderable Information</li> </ul>	nctional Modes, ection, Device

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# 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/ MSL rating/ Ball material Peak reflow		Op temp (°C)	Part marking
	('')	(2)			(0)	(4)	(5)		(0)
TRSF3221ECDB	Obsolete	Production	SSOP (DB)   16	-	-	Call TI	Call TI	0 to 70	RT21EC
TRSF3221ECDBR	Active	Production	SSOP (DB)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	RT21EC
TRSF3221ECDBR.A	Active	Production	SSOP (DB)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RT21EC
TRSF3221ECPWR	Active	Production	TSSOP (PW)   16	2000   LARGE T&R	Yes	NIPDAU   SN	Level-1-260C-UNLIM	0 to 70	RT21EC
TRSF3221ECPWR.A	Active	Production	TSSOP (PW)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RT21EC
TRSF3221EIDBR	Active	Production	SSOP (DB)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RT21EI
TRSF3221EIDBR.A	Active	Production	SSOP (DB)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RT21EI
TRSF3221EIDYYR	Active	Production	SOT-23-THIN (DYY)   16	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RT21EI
TRSF3221EIDYYR.A	Active	Production	SOT-23-THIN (DYY)   16	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RT21EI
TRSF3221EIPWR	Active	Production	TSSOP (PW)   16	2000   LARGE T&R	Yes	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	RT21EI
TRSF3221EIPWR.A	Active	Production	TSSOP (PW)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RT21EI
TRSF3221EIRGTR	Active	Production	VQFN (RGT)   16	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	F3221
TRSF3221EIRGTR.A	Active	Production	VQFN (RGT)   16	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	F3221

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No. RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



# **PACKAGE OPTION ADDENDUM**

www.ti.com 23-May-2025

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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## TAPE AND REEL INFORMATION



# TAPE DIMENSIONS KO P1 BO W Cavity A0

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TRSF3221ECDBR	SSOP	DB	16	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
TRSF3221ECPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TRSF3221EIDBR	SSOP	DB	16	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
TRSF3221EIDYYR	SOT-23- THIN	DYY	16	3000	330.0	12.4	4.8	3.6	1.6	8.0	12.0	Q3
TRSF3221EIPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TRSF3221EIRGTR	VQFN	RGT	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2



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## \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TRSF3221ECDBR	SSOP	DB	16	2000	356.0	356.0	35.0
TRSF3221ECPWR	TSSOP	PW	16	2000	356.0	356.0	35.0
TRSF3221EIDBR	SSOP	DB	16	2000	356.0	356.0	35.0
TRSF3221EIDYYR	SOT-23-THIN	DYY	16	3000	336.6	336.6	31.8
TRSF3221EIPWR	TSSOP	PW	16	2000	356.0	356.0	35.0
TRSF3221EIRGTR	VQFN	RGT	16	3000	367.0	367.0	35.0

PLASTIC SMALL OUTLINE



## NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- 5. Reference JEDEC Registration MO-345, Variation AA



PLASTIC SMALL OUTLINE



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PLASTIC SMALL OUTLINE



#### NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





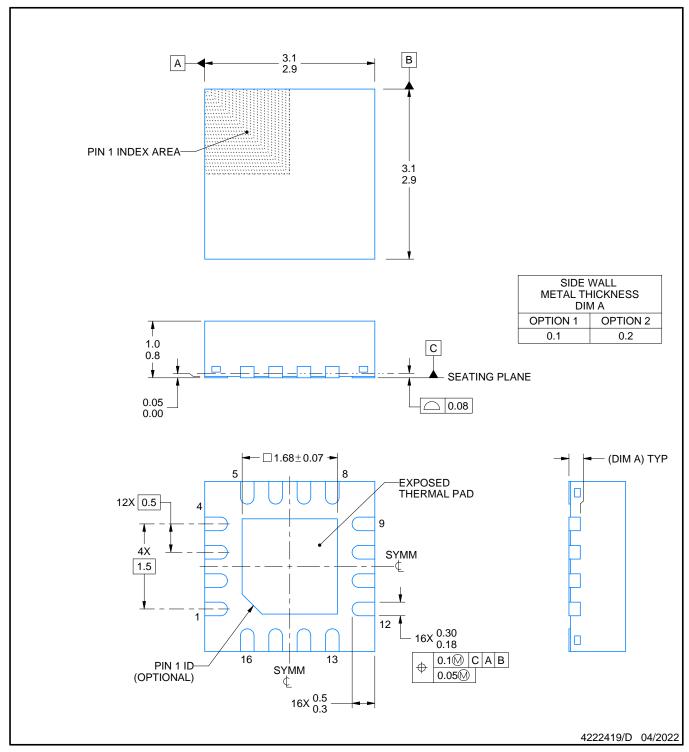
Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.







PLASTIC QUAD FLATPACK - NO LEAD

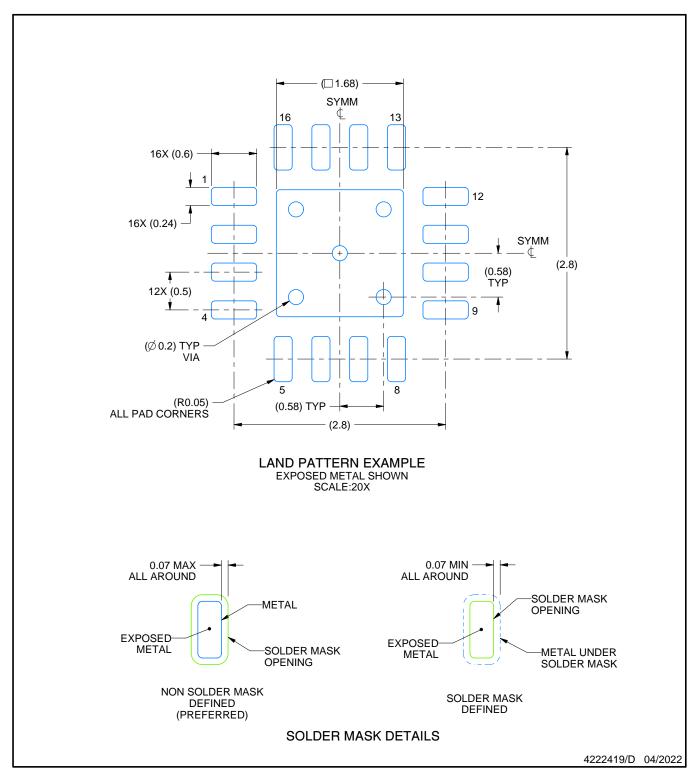


#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD

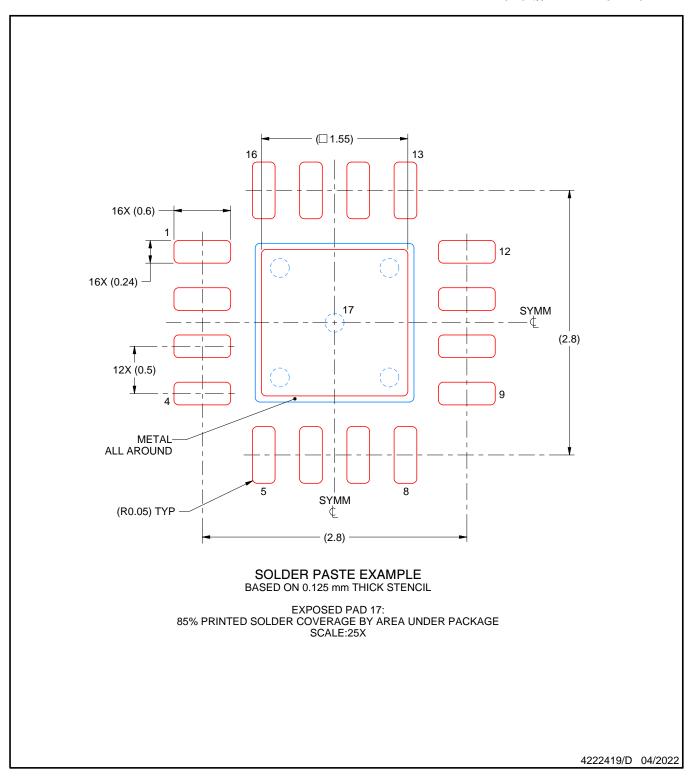


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.







#### NOTES:

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- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
  4. Reference JEDEC registration MO-150.





NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

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- 8. Board assembly site may have different recommendations for stencil design.



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